

SPTECH Silicon NPN Power Transistor

2SC940

DESCRIPTION

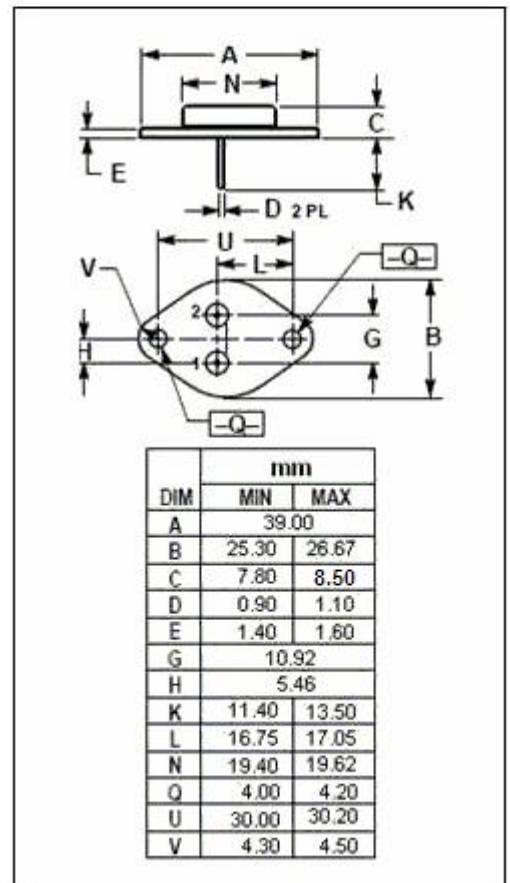
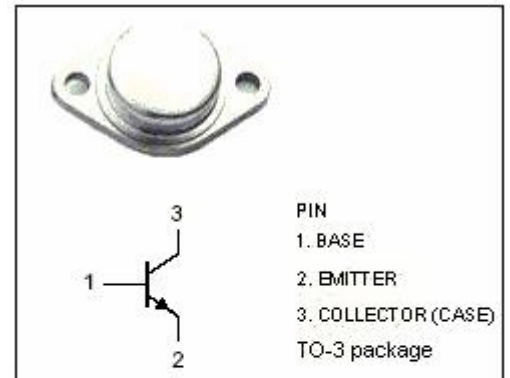
- High Breakdown Voltage-
: $V_{CEO} = 90V(\text{Min})$
- Wide Safe Operating Area

APPLICATIONS

- Designed for B/W TV horizontal deflection output applications.
- Suitable for horizontal output applications in 12~24 inch B/W TV, and switching applications of 5A class.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CES}	Collector-Emitter Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	90	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current- Continuous	7.5	A
I_{CP}	Collector Current-Pulse	15	A
P_C	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	50	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_c= 5A; I_B= 0.5A$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}= 90V; I_E= 0$			2.0	mA
h_{FE}	DC Current Gain	$I_c= 5A; V_{CE}= 5V$	15		70	
t_f	Fall Time	$I_c= 5A, I_{B1}= 0.6A$			1.0	μs

◆ **h_{FE} Classifications**

R	Q	P
15-35	25-45	35-70